

PNP Transistors

KTA1046

■ Features

- Low saturation voltage and good linearity of h_{FE} .
- Complementary to KTC2026

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

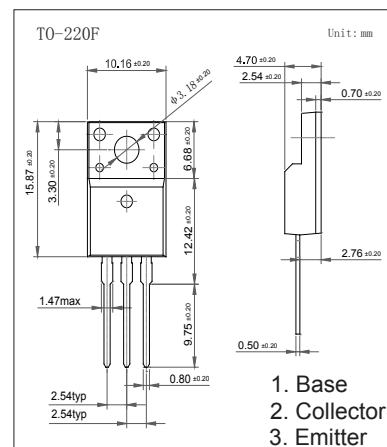
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-60	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_C	-3	A
Base Current	I_B	-0.5	
Collector Power Dissipation $T_a = 25^\circ\text{C}$ $T_c = 25^\circ\text{C}$	P_C	2	W
		25	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -10\text{ mA}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -50\text{ mA}, I_B = 0$	-60			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -10\text{ mA}, I_C = 0$	-7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -60\text{ V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7\text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{ mA}$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$			-1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	100		300	
	$h_{FE(2)}$	$V_{CE} = -5\text{ V}, I_C = -3\text{ A}$	20			
Turn-on Time	t_{on}			0.4		μs
Storage Time	t_{stg}			1.7		
Fall Time	t_f			0.5		
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		45		pF
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$		30		MHz

■ Classification of $h_{FE(1)}$

Type	KTA1046-Y	KTA1046-G
Range	100-200	160-300



PNP Transistors

KTA1046

■ Typical Characteristics

